Infusing nontrivial topology in massive Dirac fermions with scalar potential: Emergence of Scalar Hall Effect

Sumit Ghosh,1,∗ Yuriy Mokrousov,1,2 and Stefan Blügel1
1Peter Grünberg Institut (PGI-1), Forschungszentrum Jülich GmbH, 52428 Jülich, Germany
2Institute of Physics, Johannes Gutenberg-University Mainz, 55128 Mainz, Germany

We present a simplified way to access and manipulate the topology of massive Dirac fermions by tuning the scalar potential. We show systematically how a distribution of scalar potential can manipulate the signature of the gap or the mass term as well as the dispersion leading to a band inversion via inverse Klein tunnelling. In two dimensions this emergent mechanism, which we refer to as the Scalar Hall Effect, facilitates a direct drive of non-trivial topological invariants, e.g., the Chern number, and thus opens new possibilities for manipulating physical observables which originate from the nontrivial topology.

In recent years topology has become a central concept in condensed matter physics [1], while materials with non-trivial topological properties have become key in designing next generation transport and memory devices [2, 3]. An immense effort has been directed at discovering suitable materials [4, 5] and characterization of their topological classes [6, 7]. This highly active research resulted in the discovery of several new topological phases in the last decade [8, 9]. Despite a phenomenal success these studies still fail to suggest a controllable way to generate the nontrivial topological properties using external stimuli. The first topological insulator — namely the Quantum Hall Insulator — was discovered under strong magnetic field [10] which is quite challenging for any practical purpose. In materials with strong spin-orbit-coupling (SOC), such as HgTe [11] or Bi2Se3 [12], the nontrivial topological features arise from electronic interactions involving orbital and spin degrees of freedom. Such interactions can give rise to different topological phases such as the Quantum Anomalous Hall Insulator [13] and Quantum Spin Hall Insulator [14].

Despite many successful discoveries, a controllable way to generate non-trivial topological phases and drive a transition between them still remains a major challenge. In certain cases it is possible to tune the topological properties with a magnetic field [15] or magnetic impurities [16, 17], however these cases are very material specific which presents a great challenge in their applicability. For most of the cases SOC is considered to be the source of nontrivial topological properties by mediating the band inversion [18]. The band inversion is indeed an impeccable sign of a topological transition, however, on its own it does not directly reflect the specific mechanism which drives it. Besides, it is also possible to have a topological insulator even without SOC or magnetic moment [19, 20] by exploiting the symmetry of electronic degrees of freedom. A proper description of the mechanism behind inducing topological features and the transition dynamics between different topological phases is therefore highly desired in order to access and manipulate the topological phases of solid state systems.

The key to unlocking the topological properties in realistic materials lies in their dispersion which resembles that of a relativistic particle. One of the characteristic features of a relativistic dispersion is that each gap is associated with a well defined signature. For any generic Dirac spinor ψ obeying (−iγμ∂μ + m)ψ = 0 (in natural units c = ħ = 1) where γμ (μ = 0 being the temporal component) are the Dirac matrices obeying the Clifford algebra {γμ, γν} = 2ημνI with η being the Minkowski metric — the spectrum has a fundamental gap of 2m, commonly known as the mass-gap since the gap is associated with the rest mass of the particle in relativistic theory. Each energy band is associated with a particular sign of (γ0) and as a result, each gap can be identified with a specific signature. While the eigenvalue spectra remain the same irrespective of the sign of m, the eigenstates corresponding to a specific band are characterised by an opposite mass term m and therefore have completely different features. A pronounced example is the appearance of Jackiw-Rabi modes at the boundary of two different domains characterised by opposite mass terms [21] where the topological phase boundary is manifested as spatial localisation which is the essence of edge states in topological insulators.

To understand the relation between the mass term and topological characteristics of a system, let us turn to a generic 2 × 2 Dirac Hamiltonian $H = \mathbf{a} \cdot \mathbf{n}(\mathbf{R})$ defined on Bloch sphere, where $\mathbf{a}$ is the vector of Pauli matrices and $\mathbf{n}(\mathbf{R})$ is the unit vector parameterised by $\mathbf{R}$. In this case the vector Berry curvature is simply given by $\mathbf{c} \times \mathbf{R}$ [22]. In two dimensions, two of the Pauli matrices are coupled with momentum corresponding to the direction of motion while the third is coupled to the mass term. The Chern number in this case follows the same signature of the out of plane component of $\mathbf{n}$, which is nothing but the mass term. Similar correlation has been observed in two-dimensional paramagnetic systems and three dimensional complex heterostructures as well [23]. With the advent of topological insulators, condensed matter physics has become an ideal playground for immeasurable fascinating predictions originating from such relativistic
Hamiltonian as the electrons in these systems obey the relativistic dispersion relation which can be further tuned via external stimuli. They make it possible to realise several predictions of relativistic quantum mechanics such as Klein tunnelling [24], Zitterbewegung [25], and exploit these features to design novel devices with enhanced performance. In a condensed matter system the mass term is associated with a certain order parameter and therefore can be exploited to identify and manipulate different phases. On the other hand, the mass-gap originates from some internal degrees of freedom in a given material which makes it extremely difficult to control. A simple way to manipulate the magnitude and signature of the mass-gap thus has an enormous potential in fabricating new intrinsically topological systems and exploring their applications.

In this work, taking a generic two band system as a prototype, we present a systematic analysis of the topological properties in a multi-band system and demonstrate a simplified way to generate and manipulate non-trivial topological features with the help of scalar potential. In practice, such scalar potential can be introduced as an external potential difference or by the means of nanopatterning [26]. By using the two-band relativistic Dirac Hamiltonian, we demonstrate how one can manipulate the mixture of different quantum states which in turn controls the topological features. Although we present this mechanism in the context of a relativistic Hamiltonian, it is applicable to a large class of condensed matter systems as well, which facilitates a wide range of applications of this generic protocol.

Dirac equation in one dimension: In one dimension, it is sufficient to consider the $2 \times 2$ representation of Dirac matrices, which we choose here as the Pauli matrices ($\sigma$). We start by considering the impact of a scalar potential given by $V(x)\sigma_0$ where $\sigma_0$ is the identity matrix of rank 2. We define our system with the one dimensional Dirac Hamiltonian

$$H^0 = -i\sigma_1 \partial_x + \sigma_3 m + \sigma_0 V(x).$$  \hspace{1cm} (1)

In absence of the potential term, the energy spectrum consists of two hyperbolic branches separated by a gap of $2m$ with positive and negative energy eigen values characterised by positive and negative values of $\langle \sigma_3 \rangle$. For such a system, it is possible to achieve complete transmission probability if the the barrier height is greater than twice the mass term ($V_0 > 2m$) [27]. This is known as the Klein paradox [28] which has attracted a lot of interest in both high energy physics as well as in condensed matter physics [24]. The simplest way to understand the underlying mechanism is via the intermixture of states with positive and negative energy. If the scalar potential is strong enough ($V_0 > 2m$), then it can elevate the negative energy states inside the potential barrier to an energy level occupied by the positive energy states outside the barrier which creates a continuous channel using plane-

![FIG. 1. Variation of mass-gap with $V_0$. (a) Schematic of the one-dimensional periodic lattice. The dashed box shows the unit cell and the gray boxes show the scalar potential $V_0$. (b) Variation of band edges with the applied potential with shaded regions showing the energy window filled with bands and white regions correspond to the band gap. (c) Band structure for selected values of $V_0$ marked by vertical coloured lines in (b). (d) Distribution of the order parameter $\Delta(x)$ over the unit cell with red and blue colour representing the positive and negative magnitude respectively.](image)
the notion of Fermi level is not well defined. This definition will become more clear next, when we introduce the lattice model with a finite number of sites.

From Fig. 1 one can see that by increasing the barrier height it is possible to manipulate the mass gap despite the fact that $\sigma_0$ commutes with $\sigma_3$. The mass gap decreases due to the fact that the potential $V_0$ now pulls up negative energy states within the window $-m < E < m$ which can now tunnel through the region without potential where the evanescent modes have opposite signature of the mass term. In a sense, this is the Inverse Klein Tunnelling where the tunnelling happens through the potential free region. This mechanism promotes more mixing of quantum states which creates a spatial modulation of the order parameter $\Delta$. Note that at some critical values the gap vanishes completely ($V_0 = 0$) and is given by $\Delta < m/E < m$. The extension of Hamiltonian used to define the quantum spin Hall effect in HgTe-CdTe quantum wells, commonly known as the Bernevig-Hughes-Zhang (BHZ) model [11]. This is the simplest model of a Chern insulator which exhibits a Chern number $C = \text{sgn}(M)$ for $|M| < |4B|$ and $C = 0$ for $|M| > |4B|$. This lends us a perfect playground for further predictions. We start with $M = 9$, $B = 2$ and $A = 5$ which gives a trivial Chern insulator state ($C = 0$). Note that in two dimensions the mass-gap at $k_x, k_y = 0$ is given by $M - 4B$ which for our choice of parameters is 1. Here we consider a 3 × 3 supercell with one scalar impurity (resulting in 11.1% coverage) and calculate the variation of band structure, mass term and the Chern number (Fig. 2) with the variation of $V_0$. The Chern number can be calculated from

$$ C = \frac{1}{2\pi} \sum_{n} \int_{BZ} dk_x dk_y [f(E_n) - f(E_m)] \times \sum_{m \neq n} 2 \text{ Im} \left[ \langle m | \partial H/\partial k_y | n \rangle \langle n | \partial H/\partial k_x | m \rangle \right] / (E_n - E_m)^2 + \eta^2 \right) \tag{5}$$

where $n_F$ is the number of states below the Fermi level, $f(E_n)$ is the Fermi-Dirac distribution for the $n$th energy eigenvalue and $|n\rangle$ is the $n$th eigenstate. $\eta$ is the constant broadening which we choose to be 0.005. The mass term

![Figure 2](image_url)
at any particular energy is given by
\[ m(E) = \int_{BZ} dk_x dk_y \sum_{n} \langle n|\sigma_3 \otimes 1_N|n\rangle \delta(E_n - E), \]
where \( N \) is the number of sites (which for our case is 9) and \( 1_N \) is the identity matrix of rank \( N \). \( \delta(x) \) is the Dirac delta function which is approximated as a Lorentzian with broadening \( \eta \). For simplicity, instead of space resolved order parameter, we use the integrated order parameter defined as
\[ \Delta = \langle \sum_{n} \langle n|\sigma_3 \otimes 1_N|n\rangle \rangle_k = 0. \]

With these definitions one can readily see (Fig. 2) that with the increase of the scalar potential, there is a band gap closing and reopening, similar to what we observe in the one-dimensional case (Fig. 1). At the critical point, where the bands touch each other, the order parameter as well as the Chern number undergo a jump indicating a change of the topological phase. To distinguish this scalar impurity-induced emergent nontrivial effect from existing Hall effects, we call it the Scalar Hall effect. This is consistent with our earlier picture of band inversion through the mixing of different mass regimes. While in a topologically trivial regime each band is comprised of states with the same sign of the mass term, as we increase the potential, the interchange of states with opposite mass term takes place. Increase of the scalar potential enhances the mixing of states with opposite mass term and thus transports the system from a topologically trivial to nontrivial phase, characterised by a non-zero Chern number. If we start from a topologically non-trivial configuration, the additional scalar potential will enhance the topological protection as manifested in an increase of the band gap.

**Formation and manipulation of edge states:** A non-vanishing bulk topological invariant shares a direct correspondence with the existence of edge states [34, 35]. To demonstrate that, we consider a ribbon configuration, i.e. we assume a periodic boundary condition along \( x \)-direction, and periodic boundary condition along \( y \)-direction by repeating the block shown in Fig. 2a. In such a ribbon the edge states emerge when \( V_0 \) crosses the critical value at which the bulk bands cross each other (Fig. 3). Each edge hosts a single edge state such that opposite edges host states with an opposite group velocity, which is expected in case of a Chern insulator with a Chern number of 1.

One can further manipulate the behaviour of the edge states by controlling the distribution of the scalar potential. As we explained before, the scalar potential enhances the mixing between the states with an opposite mass term which causes the topological transition. In an extended system, one can use the the scalar potential selectively in different regions of space to infuse the topological nature selectively. To demonstrate this we consider the aforementioned ribbon with 3 sites along \( x \) and 90 sites along \( y \) and with scalar potential \( V_0 \) in one of every nine \( (3 \times 3) \) cells (11.1%). Then we start removing the scalar potential from one end and calculate the band structure (Fig. 4). The Fermi level \( (E_F) \) is defined as the middle of 270th and 271th eigenvalue at the \( \Gamma \)-point.

With this simple procedure one can easily manipulate the edges states selectively. By removing the scalar potential at one edge, we reduce the mixing of the states locally and as a result, the states which were sharply localised at the edges before now start moving more into the central region. This is manifested by the fact that the sharp red line in Fig. 4 remains intact as long as there are scalar potentials at the corresponding edges whereas the blue lines fade out and mix strongly with the gray bands.

**Conclusions:** In this paper we present a new paradigm to infuse non-trivial topological characteristics into a trivial insulator by means of modulating the scalar potential. The scalar potential is utilised to enhance
the mixing between different quantum states which in turn drives the system into a topologically non-trivial regime which we verified explicitly by calculating the Chern number of the system. This is further confirmed by demonstrating the appearance of the edge states with specific group velocity. In addition our method also allows to control the topological properties by local means, which is not possible with a topological insulator. We demonstrate that the edge states can be controlled by selective placement of the scalar potential. Note that although the results are shown for uniformly spaced scalar impurity, one can observe the same qualitative behaviour for randomly distributed scalar potentials as well [27]. These predictions can be realised in real materials available experimentally. Most suitable candidate for such study is a CdTe-HgTe-CdTe quantum well where the topological phases can be controlled by changing the width of the well. For Hg$_{0.33}$Cd$_{0.67}$Te-HgTe quantum well, the mass gap (2m) is $\sim$50 meV for a thickness of 50 Å [11] which indicates the scalar potential induced topological transition can be observed for $V_0 \lesssim 0.5$ eV. Our results thus open several new possibilities in controlling the topological properties and designing highly controllable devices for topological electronics.

Acknowledgments: SG would like to acknowledge helpful discussions with Emil Prodan.

FIG. 4. Variation of the band structure with the distribution of the scalar potential along the ribbon. (a) The band structure when the full width of the ribbon is covered with the potential. (b,c) show the band structure with $2/3$- and $1/3$-coverage, and (d) shows the band structure with no potential. Inset of each figure shows the spatial distribution where the black dots represent the scalar impurity. Red and blue colours denote the $y = 1$ and $y = 90$ edges (Fig. 3a).

References:

[27] “Supplementary materials,” (****).
SUPPLEMENTARY MATERIALS

Transmission of massive Dirac particle in one dimension through a rectangular barrier

Here we briefly show the transmission of a massive Dirac particle through a scalar potential. We start with a massive Dirac equation in two dimensions given by

\[ H_1^D = -i\sigma_1 \partial_x + \sigma_3 m + \sigma_0 V(x), \quad (8) \]

where \( m \) is the mass term which we choose to be 1. \( \sigma_{1,3} \) are the Pauli matrices and \( \sigma_0 \) is the identity matrix of rank 2. The simplest way to study the impact of a scalar potential is to introduce a rectangular barrier of width \( w \), such that \( V(x) = V_0 \) for \(-w/2 \leq x \leq w/2\) and \( V(x) = 0 \) otherwise. The transmission probability for such a rectangular barrier is given by

\[ T = \frac{16|\lambda|/(1 + \lambda)^2 e^{-i\kappa_2 w} - (1 - \lambda)^2 e^{i\kappa_2 w}|^2}{\lambda^2 E - m^2 + \lambda \sqrt{(E - V_0)^2 - m^2}}. \]

For such a system, it is possible to achieve complete transmission if the barrier height is greater than twice the mass term \( (V_0 > 2m) \). This is manifested as multiple transmission channels for \( E < V_0 \) in Fig. 5.

![Fig. 5](image)

**Fig. 5.** Variation of transmission probability for different energy and barrier width in case of a rectangular barrier introduced in a one-dimensional Dirac Hamiltonian. Here we choose \( V_0 = 4 \) and \( m = 1 \).

For \( w \to \infty \), the Klein window \((m \leq E \leq V_0 - m)\) can manifest complete transmission. At this limit the region inside and outside the scalar potential are dominated by a particular sign of the mass term. For small \( w \), there is more mixture between the states with different mass term which manifests itself as a modulation of the transmission probability with respect to the energy on both side of the forbidden zone \((V_0 - m \leq E \leq V_0 + m)\). In a periodic lattice with fixed width of the potential region, this interference results in a modulation of mass-gap with respect to the barrier height \( V_0 \).

**Lattice model in one dimension: Variation of band gap with barrier height**

Here we show the variation of band structure and band gap of a one dimensional discrete periodic lattice with respect to the barrier height. We start with the one dimensional modified Creutz lattice given by

\[ H_1(k) = (M - 2B \cos(k))\sigma_3 + 2A \sin(k)\sigma_1 \quad (9) \]

Here we choose \( M = A = 5.0 \) and \( B = 2.0 \), and a super cell with \( L = 40 \) sites. A scalar potential of strength \( V_0 \) is spanned over a region of \( a = 16 \) sites, i.e. 40% of it is covered with the scalar potential. The Fermi level corresponds to half filling and is kept at 0. We define a site-resolved order parameter

\[ \Delta_i = \left| \left( \langle +i|\sigma_3|+i \rangle - \langle -i|\sigma_3|-i \rangle \right)/2 \right|_{k=0}, \quad (10) \]

where \( |+,i \rangle \) and \( |-,i \rangle \) is the wave function at site \( i \) of the lowest positive energy and highest negative energy states. The total order parameter is defined as \( \Delta = \sum_i \Delta_i \). In addition we define the effective mass term at a given energy \( E \) as

\[ m(E) = \int_{-\pi/L}^{\pi/L} dk \sum_{n} \langle n|\sigma_3 \otimes I_L|n \rangle \delta(E_n - E) \quad (11) \]

where \( I_L \) is the identity matrix of order \( L \). \( \delta(E) \) is the Dirac delta function which is approximated with a Lorentzian with a broadening of 0.005.

From Fig. 6 one can readily see that the variation of the band gap in the lattice model is qualitatively the same as the prediction of the continuum model. This establishes the validity of the lattice model for our study. From the band structures one can see that the distribution of the mass term switches sign as it passes through a
band crossing (denoted by vertical dashed lines in Fig. 6). This is also manifested as a jump in total order parameter (Fig. 6e). Note that the jump is prominent only at the first crossing point near $V_0 = 4$. This is because the change in $m(E)$ is caused by the region with finite potential which is elevated in energy by $V_0$ (as denoted by the blue regions for positive spectrum in Fig. 6b-d). The situation becomes more intriguing in two dimensions where one can clearly see the change of topological properties of the system with $V_0$.

**Random orientation of potential**

Here we demonstrate that the scalar Hall effect is possible even with a random distribution of scalar potential. First we consider a $12 \times 12$ lattice with 16 scalar potential (11.1% coverage) and calculate the band structure and Chern number. Since calculating Chern number for such large system is computationally quite demanding, we calculate the Chern number for two different topological phases.

Similar behaviour can be observed with a ribbon with open boundary condition along $y$ direction. We choose a unit cell of $15 \times 60$ sites and scatter 100 potential site with $V_0 = 20$.

From Fig. 7 and Fig. 8 one can readily see that the change of topological properties by scalar impurity is not restricted to periodic distribution and can be observed for any any arbitrary distribution.